

2N2219, 2N2219A, 2N2219AL

Small Signal Switching Transistor

NPN Silicon

Features

- MIL-PRF-19500/251 Qualified
- Available as JAN, JANTX, and JANTXV

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	50	Vdc
Collector - Base Voltage	V_{CBO}	75	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	800	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_T	0.8	W
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_T	3.0	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

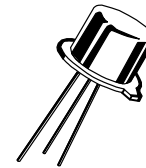
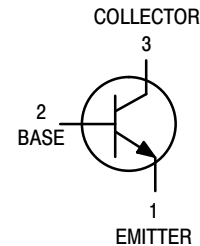
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

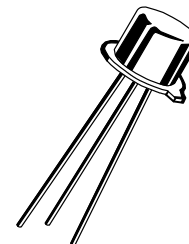


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<http://onsemi.com>



TO-39
CASE 205AB
(2N2219, 2N2219A)



TO-5
CASE 205AA
(2N2219AL)

ORDERING INFORMATION

Device	Package	Shipping
JAN2N2219/A	TO-39	Bulk
JANTX2N2219/A		
JANTXV2N2219/A		
JAN2N2219AL	TO-5	Bulk
JANTX2N2219AL		
JANTXV2N2219AL		

2N2219, 2N2219A, 2N2219AL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ($I_E = 10\text{ mA}$)	$V_{(BR)CEO}$	30 50	– –	Vdc
Emitter–Base Cutoff Current ($V_{EB} = 5.0\text{ Vdc}$) ($V_{EB} = 6.0\text{ Vdc}$) ($V_{EB} = 4.0\text{ Vdc}$)	I_{EBO}	– – –	10 10 10	μAdc μAdc nAdc
Collector–Emitter Cutoff Current ($V_{CE} = 30\text{ Vdc}$) ($V_{CE} = 50\text{ Vdc}$)	I_{CES}	– –	10 10	nAdc nAdc
Collector–Base Cutoff Current ($V_{CB} = 50\text{ Vdc}$) ($V_{CB} = 60\text{ Vdc}$) ($V_{CB} = 60\text{ Vdc}$) ($V_{CB} = 75\text{ Vdc}$)	I_{CBO}	– – – –	10 10 10 10	nAdc μAdc nAdc μAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 0.1\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 150\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	35 50 50 75 75 100 100 30	– – 325 325 – – 300 –	–
Collector–Emitter Saturation Voltage ($I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$) ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{CE(sat)}$	– – – –	0.4 0.3 1.6 1.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$) ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{BE(sat)}$	0.6 0.6 – –	1.3 1.2 2.6 2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Magnitude of Small–Signal Current Gain ($I_C = 20\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	$ h_{fe} $	2.5	12	–
Small–Signal Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ kHz}$)	h_{fe}	50 75	– –	–
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$)	C_{ibo}	–	25	pF

SWITCHING CHARACTERISTICS

Turn–On Time (Reference Figure in MIL–PRF–19500/251)	t_{on}	– –	40 35	ns
Turn–Off Time (Reference Figure in MIL–PRF–19500/251)	t_{off}	– –	250 300	ns

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

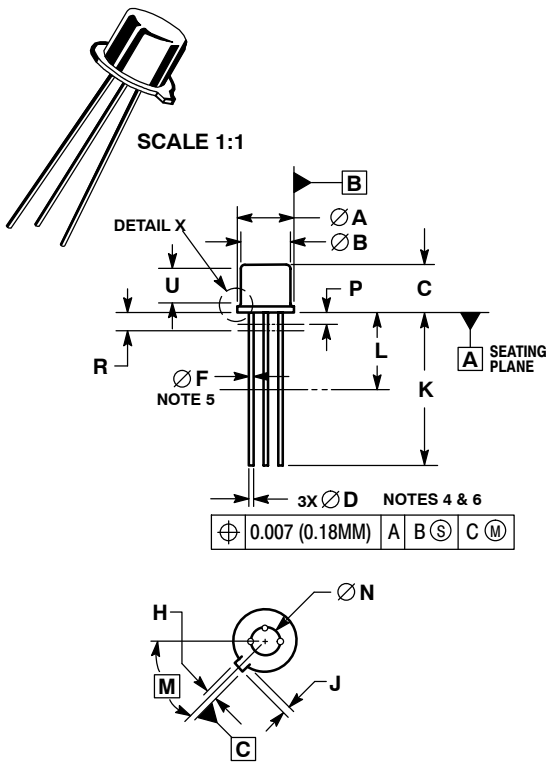
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



TO-5 3-Lead CASE 205AA ISSUE B

DATE 06 JUL 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
 4. LEAD TRUE POSITION TO BE DETERMINED AT THE GAUGE PLANE DEFINED BY DIMENSION R.
 5. DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
 6. DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
 7. BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A, B, AND T.
 8. DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.89	9.40	0.350	0.370
B	8.00	8.51	0.315	0.335
C	6.10	6.60	0.240	0.260
D	0.41	0.53	0.016	0.021
E	0.23	3.18	0.009	0.125
F	0.41	0.48	0.016	0.019
H	0.71	0.86	0.028	0.034
J	0.73	1.02	0.029	0.040
K	38.10	44.45	1.500	1.750
L	6.35	---	0.250	---
M	45° BSC		45° BSC	
N	5.08 BSC		0.200 BSC	
P	---	1.27	---	0.050
R	1.37 BSC		0.054 BSC	
T	---	0.76	---	0.030
U	2.54	---	0.100	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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DESCRIPTION:	TO-5 3-LEAD	PAGE 1 OF 2

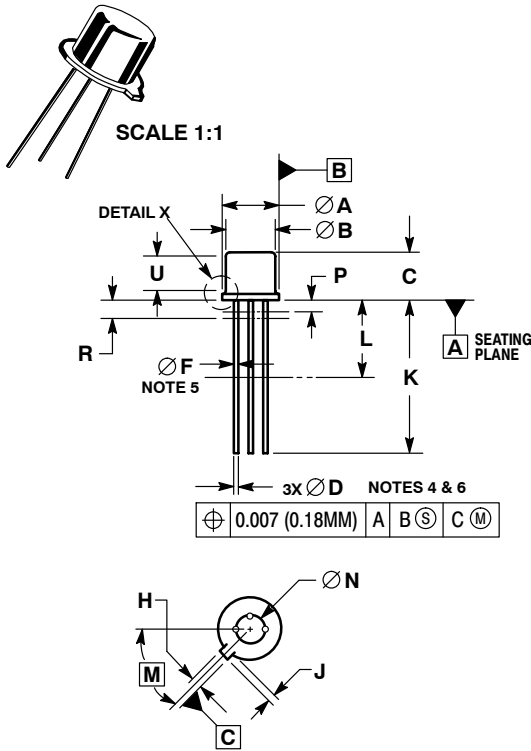
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



TO-39 3-Lead
CASE 205AB
ISSUE A

DATE 25 JUN 2012



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
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B	8.00	8.51	0.315	0.335
C	6.10	6.60	0.240	0.260
D	0.41	0.48	0.016	0.019
E	0.23	3.18	0.009	0.125
F	0.41	0.48	0.016	0.019
H	0.71	0.86	0.028	0.034
J	0.73	1.02	0.029	0.040
K	12.70	14.73	0.500	0.580
L	6.35	---	0.250	---
M	45° BSC		45° BSC	
N	5.08 BSC		0.200 BSC	
P	---	1.27	---	0.050
R	1.37 BSC		0.054 BSC	
T	---	0.76	---	0.030
U	2.54	---	0.100	---

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DESCRIPTION:	TO-39 3-LEAD	PAGE 1 OF 2

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